



# MMDT3904VC

# DUAL NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

#### **Features**

Epitaxial Planar Die Construction

Ideal for Low Power Amplification and Switching

Ultra-Small Surface Mount Package

Lead Free By Design/RoHS Compliant (Note 4)

"Green Device" (Note 5)

#### **Mechanical Data**

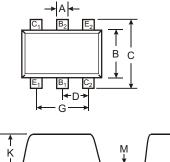
Case: SOT-563

Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0

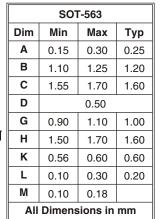
Moisture Sensitivity: Level 1 per J-STD-020C Terminals: Finish - Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208

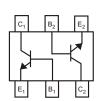
Terminal Connections: See Diagram

Marking (See Page 2): APK
Ordering Information: See Below
Date Code Information: See Page 2
Weight: 0.003 grams (approximate)



SEE NOTE 1





### Maximum Ratings @ T<sub>A</sub> = 25 C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current - Continuous	Ic	200	mA
Power Dissipation (Note 2)	P <sub>d</sub>	200	mW
Thermal Resistance, Junction to Ambient	R JA	625	C/W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	С

#### Ordering Information (Note 3)

Device	Packaging	Shipping		
MMDT3904VC-7	SOT-563	3000/Tape & Reel		

Notes

- 1. Package is non-polarized. Parts may be on reel in orientation illustrated, 180 rotated, or mixed (both ways).
- 2. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 3. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.
- 4. No purposefully added lead.
- 5. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.

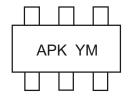


## Electrical Characteristics @ T<sub>A</sub> = 25 C unless otherwise specified

Characteristic	Symbol	Symbol Min		Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)						
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	60		V	I <sub>C</sub> = 10 A, I <sub>E</sub> = 0	
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	40		V	I <sub>C</sub> = 1.0mA, I <sub>B</sub> = 0	
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	5.0		V	I <sub>E</sub> = 10 A, I <sub>C</sub> = 0	
Collector Cutoff Current	I <sub>CEX</sub>		50	nA	V <sub>CE</sub> = 30V, V <sub>EB(OFF)</sub> = 3.0V	
Base Cutoff Current	I <sub>BL</sub>	I <sub>BL</sub> 50		nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$	
ON CHARACTERISTICS (Note 6)	,		•	•		
DC Current Gain	h <sub>FE</sub>	40 70 100 60 30	300		$ \begin{array}{ c c c c c c }\hline & I_C = 100\mu\text{A},  V_{CE} = 1.0\text{V}\\ I_C = 1.0\text{mA},  V_{CE} = 1.0\text{V}\\ I_C = 10\text{mA},  V_{CE} = 1.0\text{V}\\ I_C = 50\text{mA},  V_{CE} = 1.0\text{V}\\ I_C = 100\text{mA},  V_{CE} = 1.0\text{V}\\ \end{array} $	
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>		0.20 0.30	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1.0mA I <sub>C</sub> = 50mA, I <sub>B</sub> = 5.0mA	
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	0.65	0.85 0.95	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1.0mA I <sub>C</sub> = 50mA, I <sub>B</sub> = 5.0mA	
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C <sub>obo</sub>		4.0	pF	$V_{CB} = 5.0V$ , $f = 1.0MHz$ , $I_E = 0$	
Input Capacitance	C <sub>ibo</sub>		8.0	pF	$V_{EB} = 0.5V$ , $f = 1.0MHz$ , $I_{C} = 0$	
Input Impedance	h <sub>ie</sub>	1.0	10	k		
Voltage Feedback Ratio	h <sub>re</sub>	0.5	8.0	x 10 <sup>-4</sup>	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1.0mA,	
Small Signal Current Gain	h <sub>fe</sub>	100	400		f = 1.0kHz	
Output Admittance	h <sub>oe</sub>	1.0	40	S		
Current Gain-Bandwidth Product	f <sub>T</sub>	300		MHz	V <sub>CE</sub> = 20V, I <sub>C</sub> = 10mA, f = 100MHz	
Noise Figure	NF		5.0	dB	V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 100 A, R <sub>S</sub> = 1.0k f = 1.0kHz	
SWITCHING CHARACTERISTICS	,		•	•	•	
Delay Time	t <sub>d</sub>		35	ns	V <sub>CC</sub> = 3.0V, I <sub>C</sub> = 10mA,	
Rise Time	t <sub>r</sub>		35	ns	$V_{BE(off)} = -0.5V, I_{B1} = 1.0mA$	
Storage Time	t <sub>s</sub>		200	ns	V <sub>CC</sub> = 3.0V, I <sub>C</sub> = 10mA,	
Fall Time	t <sub>f</sub>		50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$	

Notes: 6. Short duration test pulse used to minimize self-heating.

# **Marking Information**



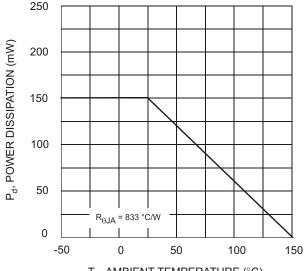
APK = Product Type Marking Code YM = Date Code Marking Y = Year ex: R = 2004 M = Month ex: 9 = September

Date Code Key

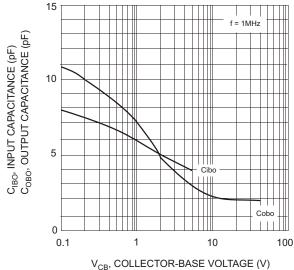
Year	2005	2006	2007	2008	2009	2010	2011	2012
Code	S	Т	U	V	W	X	Υ	Z

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

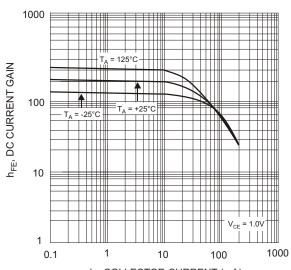




T<sub>A</sub>, AMBIENT TEMPERATURE (°C) Fig. 1, Derating Curve - Total



V<sub>CB</sub>, COLLECTOR-BASE VOLTAGE (V) Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage



I<sub>C</sub>, COLLECTOR CURRENT (mA) Fig. 3, Typical DC Current Gain vs Collector Current

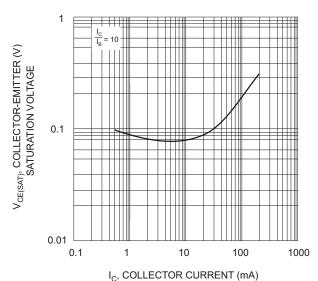


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

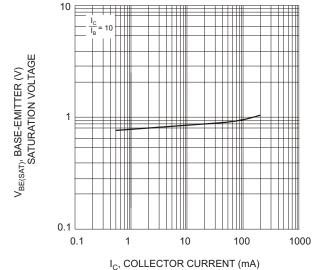


Fig. 5, Typical Base-Emitter
Saturation Voltage vs. Collector Current



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